

INCHANGE SEMICONDUCTOR

Isc N-Channel MOSFET Transistor

STW20NM50FD

FEATURES

- · Low input capacitance and gate charge
- · Low gate input resistance
- 100% avalanche tested
- · Tight process control and high manufacturing yields
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

Switching application

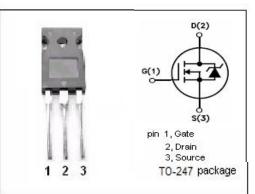
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

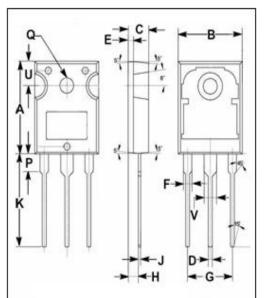
| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|--|----------|------|--|
| V _{DSS} | Drain-Source Voltage | 500 | V | |
| V _{GSS} | Gate-Source Voltage | ±30 | V | |
| I _D | Drain Current-Continuous@Tc=25℃ Tc=100℃ | 20 14 | А | |
| I _{DM} | Drain Current-Single Pulsed | 80 | А | |
| P _D | Total Dissipation | 214 | W | |
| Tj | Max. Operating Junction Temperature | 150 | °C | |
| T _{stg} | Storage Temperature | -65~150 | °C | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | | UNIT | |
|-----------|---------------------------------------|------|--------------|--|
| Rth(ch-c) | Channel-to-case thermal resistance | 0.59 | °C/W | |
| Rth(ch-a) | Channel-to-ambient thermal resistance | 30 | °C /W | |

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| | mm | | |
|-----|-------|-------|--|
| DIM | MIN | MAX | |
| Α | 19.80 | 20.20 | |
| В | 15.40 | 15.80 | |
| C | 4.90 | 5.10 | |
| D | 0.90 | 1.10 | |
| E | 1.40 | 1.60 | |
| F | 1.90 | 2.10 | |
| G | 10.80 | 11.00 | |
| Η | 2.40 | 2.60 | |
| J | 0.50 | 0.70 | |
| K | 19.50 | 20.50 | |
| P | 3.90 | 4.10 | |
| Q | 3.30 | 3.50 | |
| U | 5.20 | 5.40 | |
| V | 2.90 | 3.10 | |

isc website: www.iscsemi.cn



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ELECTRICAL CHARACTERISTICS

$T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|----------------------|--------------------------------|---|-----|-----|---------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D = 0.25mA | 500 | | | V |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} =±30V; I _D =0.25mA | 3 | | 5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D =10A | | 220 | 250 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±30V;V _{DS} =0V | | | ±0.1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = 600V; V _{GS} = 0V; T _J =25°C T _J =125°C | | | 1 10 | μA |
| V _{SDF} | Diode forward voltage | I _{SD} =20A, V _{GS} = 0 V | | | 1.5 | V |

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